Product data sheet

1. General description

PNP low V_{CEsat} transistor in a SOT89 (SC-62) flat lead Surface-Mounted Device (SMD) plastic package.

NPN complement: PBSS4250X

2. Features and benefits

- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- · Higher efficiency leading to less heat generation
- · Reduced printed-circuit board requirements
- AEC-Q101 qualified

3. Applications

- Power management
 - · DC/DC converters
 - · Supply line switching
 - Battery charger
 - LCD backlighting
- Peripheral drivers
 - Driver in low supply voltage applications (e.g. lamps and LEDs).
 - Inductive load driver (e.g. relays, buzzers and motors)

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V _{CEO}	collector-emitter voltage	open base	-	-	-50	V
I _C	collector current		-	-	-2	Α
h _{FE}	DC current gain	$V_{CE} = -2 \text{ V}; I_{C} = -0.1 \text{ A}; T_{amb} = 25 ^{\circ}\text{C}$	200	-	-	



50 V, 2 A PNP low VCEsat transistor

5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	Е	emitter		С
2	С	collector		, , , , , , , , , , , , , , , , , , ,
3	В	base	3 2 1	B—[
			SOT89	sym132

6. Ordering information

Table 3. Ordering information

Type number	Package					
	Name	Description	Version			
PBSS5250X	SOT89	plastic, surface-mounted package; 3 leads; 1.5 mm pitch; 4.5 mm x 2.5 mm x 1.5 mm body	SOT89			

7. Marking

Table 4. Marking codes

Type number	Marking code[1]
PBSS5250X	%1L

[1] % = placeholder for manufacturing site code

8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V_{CBO}	collector-base voltage	open emitter		-	-50	V
V_{CEO}	collector-emitter voltage	open base		-	-50	V
V _{EBO}	emitter-base voltage	open collector		-	-5	V
I _C	collector current			-	-2	А
I _{CM}	peak collector current	limited by T _{j(max)}		-	-5	А
I _B	base current			-	-0.5	А
P _{tot}	total power dissipation	T _{amb} ≤ 25 °C	[1]	-	550	mW
			[2]	-	1	W
Tj	junction temperature			-	150	°C
T _{amb}	ambient temperature			-65	150	°C
T _{stg}	storage temperature			-65	150	°C

- 1] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided, 35 μm copper, tin-plated, mounting pad for collector 1 cm².

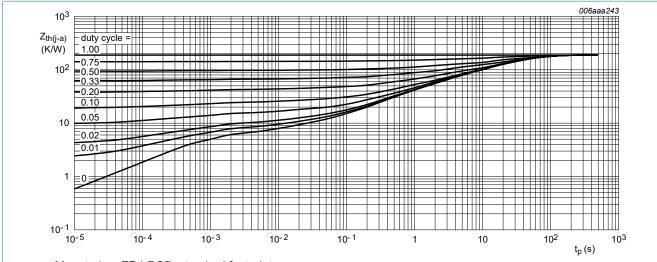
50 V, 2 A PNP low VCEsat transistor

9. Thermal characteristics

Table 6. Thermal characteristics

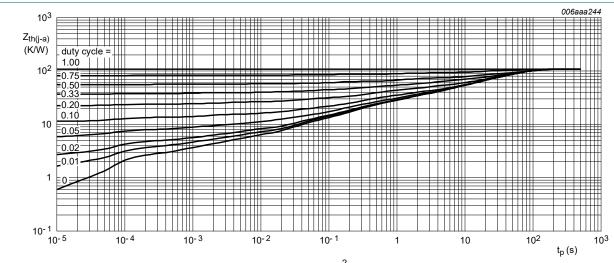
Symbol	Parameter	Conditions		Min	Tvn	Max	Unit
Symbol	Parameter	Conditions		IVIIII	Тур	IVIAX	Unit
R _{th(j-a)} thermal resistance from junction to ambient		[1]	-	-	225	K/W	
	junction to ambient		[2]	-	-	125	K/W
			[3]	-	-	90	K/W
			[4]	-	-	80	K/W
$R_{th(j-sp)}$	thermal resistance from junction to solder point			-	-	16	K/W

- Device mounted on an FR4 PCB, single-sided, 35 μm copper, tin-plated and standard footprint.
- [2] Device mounted on an FR4 PCB, single-sided, 35 µm copper, tin-plated, mounting pad for collector 1 cm².
- Device mounted on an FR4 PCB, single-sided, $35 \, \mu m$ copper, tin-plated, mounting pad for collector $6 \, cm^2$. Device mounted on a ceramic PCB, $7 \, cm^2$, single-sided, $35 \, \mu m$ copper, tin-plated; standard footprint. [3]
- [4]



Mounted on FR4 PCB; standard footprint.

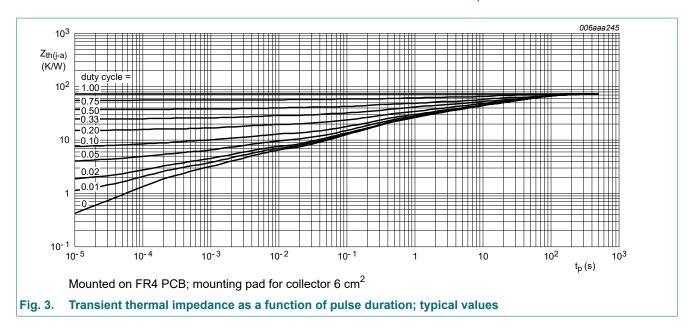
Transient thermal impedance as a function of pulse duration; typical values Fig. 1.



Mounted on FR4 PCB; mounting pad for collector 1 cm²

Transient thermal impedance as a function of pulse duration; typical values

50 V, 2 A PNP low VCEsat transistor



10. Characteristics

Table 7. Characteristics

Symbol	Parameter	Conditions	M	lin	Тур	Max	Unit
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = -100 \mu A; I_E = 0 A; T_{amb} = 25 °C$	-5	50	-	-	V
V _{(BR)CEO}	collector-emitter breakdown voltage	$I_C = -2 \text{ mA}; I_B = 0 \text{ A}; T_{amb} = 25 \text{ °C}$	-5	50	-	-	V
V _{(BR)EBO}	emitter-base breakdown voltage (collector open)	$I_E = -100 \mu A; I_C = 0 A; T_{amb} = 25 °C$	-5	5	-	-	V
I _{CBO}	collector-base cut-off	$\begin{split} & _{C} = -100 \ \mu A; \ _{E} = 0 \ A; \ T_{amb} = 25 \ ^{\circ}C \\ & _{C} = -2 \ mA; \ _{B} = 0 \ A; \ T_{amb} = 25 \ ^{\circ}C \\ & _{E} = -100 \ \mu A; \ _{C} = 0 \ A; \ T_{amb} = 25 \ ^{\circ}C \\ & _{C} = -2 \ mA; \ _{E} = 0 \ A; \ T_{amb} = 25 \ ^{\circ}C \\ & _{C} = -50 \ V; \ _{E} = 0 \ A; \ T_{amb} = 25 \ ^{\circ}C \\ & _{C} = -2 \ V; \ _{C} = 0 \ A; \ T_{amb} = 25 \ ^{\circ}C \\ & _{C} = -2 \ V; \ _{C} = 0.1 \ A; \ T_{amb} = 25 \ ^{\circ}C \\ & _{C} = -2 \ V; \ _{C} = -0.1 \ A; \ T_{amb} = 25 \ ^{\circ}C \\ & _{C} = -2 \ V; \ _{C} = -1 \ A; \ pulsed; \ t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb} = 25 \ ^{\circ}C \\ & _{C} = -2 \ V; \ _{C} = -2 \ A; \ pulsed; \ t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb} = 25 \ ^{\circ}C \\ & _{C} = -0.5 \ A; \ _{B} = -50 \ mA; \ T_{amb} = 25 \ ^{\circ}C \\ & _{C} = -2 \ A; \ _{B} = -50 \ mA; \ T_{amb} = 25 \ ^{\circ}C \\ & _{C} = -2 \ A; \ _{B} = -200 \ mA; \ pulsed; \ t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb} = 25 \ ^{\circ}C \\ & _{C} = -2 \ A; \ _{B} = -200 \ mA; \ pulsed; \ t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb} = 25 \ ^{\circ}C \\ & _{C} = -2 \ A; \ _{B} = -200 \ mA; \ pulsed; \ t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb} = 25 \ ^{\circ}C \\ & _{C} = -2 \ A; \ _{B} = -200 \ mA; \ pulsed; \ t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb} = 25 \ ^{\circ}C \\ & _{C} = -2 \ A; \ _{B} = -200 \ mA; \ pulsed; \ t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb} = 25 \ ^{\circ}C \\ & _{C} = -2 \ A; \ _{C} = -200 \ mA; \ pulsed; \ t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb} = 25 \ ^{\circ}C \\ & _{C} = -2 \ A; \ _{C} = -200 \ mA; \ pulsed; \ t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb} = 25 \ ^{\circ}C \\ & _{C} = -2 \ A; \ _{C} = -200 \ mA; \ pulsed; \ t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb} = 25 \ ^{\circ}C \\ & _{C} = -2 \ A; \ _{C} = -200 \ mA; \ pulsed; \ t_{p} \le 300 \ \mu s; \ \delta \le 0.02; \ T_{amb} = 25 \ ^{\circ}C \\ & _{C} = -2 \ A; \ _{C} = -2 \$	-	-100	nA		
	current emitter-base cut-off	$V_{CB} = -50 \text{ V}; I_E = 0 \text{ A}; T_j = 150 ^{\circ}\text{C}$	-		-	-50	μΑ
I _{EBO}	emitter-base cut-off current	V _{EB} = -5 V; I _C = 0 A; T _{amb} = 25 °C	-		-	-100	nA
I _{CES}	collector-emitter cut-off current	$V_{CE} = -50 \text{ V}; V_{BE} = 0 \text{ V}; T_{amb} = 25 \text{ °C}$	-		-	-100	nA
h _{FE}	DC current gain	V _{CE} = -2 V; I _C = -0.1 A; T _{amb} = 25 °C	20	00	-	-	
		V _{CE} = -2 V; I _C = -0.5 A; T _{amb} = 25 °C	20	00	-	-	
			20	00	-	-	
			10	00	-	-	
V _{CEsat}	collector-emitter	$I_C = -0.5 \text{ A}; I_B = -50 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	-		-	-90	mV
	saturation voltage	I _C = -1 A; I _B = -50 mA; T _{amb} = 25 °C	-		-	-250	mV
		$I_C = -2 \text{ A}; I_B = -100 \text{ mA}; T_{amb} = 25 ^{\circ}\text{C}$	-		-	-380	mV
			-		-	-320	mV
R _{CEsat}	collector-emitter saturation resistance	300 μs; δ ≤ 0.02; T _{amb} = 25 °C	-		-	160	mΩ
V_{BEsat}	base-emitter saturation voltage	$I_C = -2 \text{ A}$; $I_B = -100 \text{ mA}$; $T_{amb} = 25 \text{ °C}$	-		-	-1.1	V

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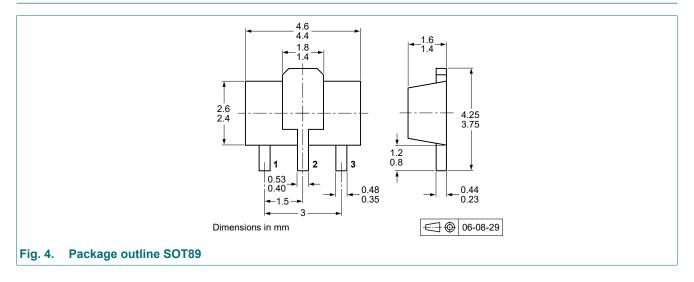
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = -2 \text{ V; } I_{C} = -1 \text{ A; } T_{amb} = 25 \text{ °C}$	-1.1	-	-	V
f _T	transition frequency	V_{CE} = -5 V; I_{C} = -100 mA; f = 100 MHz; T_{amb} = 25 °C	100	-	-	MHz
C _c	collector capacitance	V_{CB} = -10 V; I_E = 0 A; I_e = 0 A; I_e = 1 MHz; I_{CB} = 25 °C	-	-	35	pF

11. Test information

Quality information

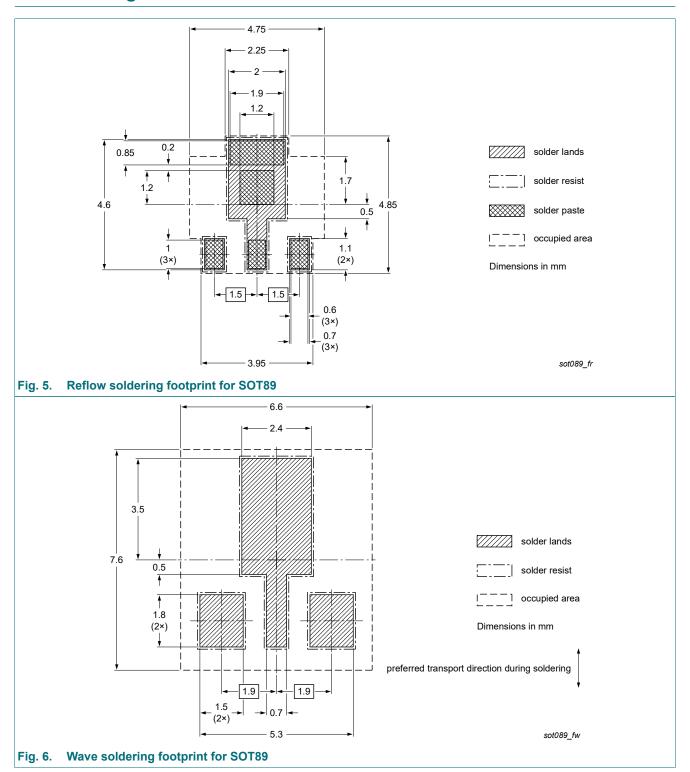
This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard Q101 - *Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

12. Package outline



50 V, 2 A PNP low VCEsat transistor

13. Soldering



50 V, 2 A PNP low VCEsat transistor

14. Revision history

Table 8. Revision history

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Data sheet ID	Release date	Data sheet status	Change notice	Supersedes		
PBSS5250X v.3	20230424	Product data sheet	-	PBSS5250X v.2		
Modifications:	of Nexperia	 The format of this data sheet has been redesigned to comply with the identity guidelines of Nexperia. Legal texts have been adapted to the new company name where appropriate. 				
PBSS5250X v.2	20041104	Product data sheet	-	PBSS5250X v.1		
PBSS5250X v.1	20030617	Product specification	-	-		

50 V, 2 A PNP low VCEsat transistor

15. Legal information

Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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